

REDUNDANT INTERCONNECT HIGH CURRENT BIPOLAR DEVICE AND  
METHOD OF FORMING THE DEVICE

ABSTRACT OF THE DISCLOSURE

A bipolar transistor having a base contact surrounded by an emitter contact. A plurality of wires extending from the base contact and the emitter contact of the bipolar transistor, wherein the wires of the base contact are stacked higher than the wires of the emitter contact. A device comprising a plurality of 5 wires of the emitter contact, wherein at least one side of each emitter contact abuts each adjacent transistor. Increasing the wiring stack of each row of transistors in the device as the distance between the row and the current input increases.